

Atomic scale insights into the epitaxial growth mechanism of 2D Cr_3Te_4 on mica

Supplementary Information

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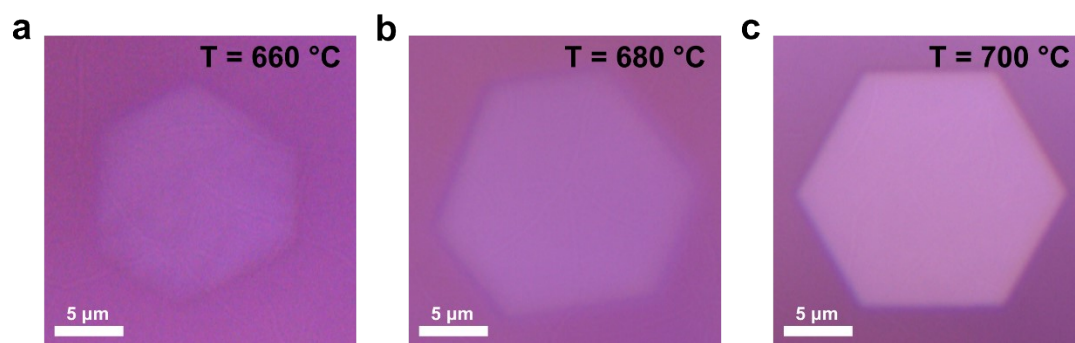


Fig. S1 Optical images taken from typical Cr_3Te_4 samples obtained by various growth temperatures, for a growth temperature (T) of 660°C (a), 680°C (b), and 700°C (c), respectively. The thickness of the nanoplates shown is ~15 nm in S1a, ~37 nm in S1b, and ~80 nm in S1c. This indicates that the thickness of the nanoplates can be reduced by a decreased growth temperature in the chemical vapour deposition process.